

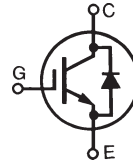
**900V XPT™ IGBTs**  
**GenX3™ w/Diode**
**IXYA8N90C3D1**  
**IXYP8N90C3D1**

$$V_{CES} = 900V$$

$$I_{C110} = 8A$$

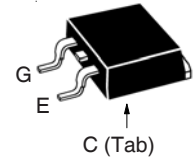
$$V_{CE(sat)} \leq 2.5V$$

$$t_{fi(typ)} = 130ns$$

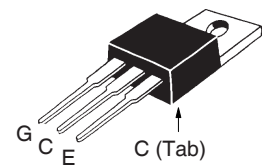
 High-Speed IGBT  
 for 20-50 kHz Switching


Symbol	Test Conditions	Maximum Ratings	
$V_{CES}$	$T_J = 25^\circ C$ to $175^\circ C$	900	V
$V_{CGR}$	$T_J = 25^\circ C$ to $175^\circ C$ , $R_{GE} = 1M\Omega$	900	V
$V_{GES}$	Continuous	$\pm 20$	V
$V_{GEM}$	Transient	$\pm 30$	V
$I_{C25}$	$T_C = 25^\circ C$	20	A
$I_{C110}$	$T_C = 110^\circ C$	8	A
$I_{F110}$	$T_C = 110^\circ C$	12	A
$I_{CM}$	$T_C = 25^\circ C$ , 1ms	48	A
$I_A$	$T_C = 25^\circ C$	4	A
$E_{AS}$	$T_C = 25^\circ C$	15	mJ
<b>SSOA</b>	$V_{GE} = 15V$ , $T_{VJ} = 150^\circ C$ , $R_G = 30\Omega$	$I_{CM} = 16$	A
<b>(RBSOA)</b>	Clamped Inductive Load	@ $V_{CE} \leq V_{CES}$	
$P_C$	$T_C = 25^\circ C$	125	W
$T_J$		-55 ... +175	$^\circ C$
$T_{JM}$		175	$^\circ C$
$T_{stg}$		-55 ... +175	$^\circ C$
$T_L$	Maximum Lead Temperature for Soldering	300	$^\circ C$
$T_{SOLD}$	1.6 mm (0.062in.) from Case for 10s	260	$^\circ C$
$M_d$	Mounting Torque (TO-220)	1.13/10	Nm/lb.in.
$F_C$	Mounting Force (TO-263)	10..65 / 2.2..14.6	N/lb.
<b>Weight</b>	TO-263	2.5	g
	TO-220	3.0	g

TO-263 AA (IXYA)



TO-220AB (IXYP)



G = Gate      C = Collector  
 E = Emitter    Tab = Collector

**Features**

- Optimized for Low Switching Losses
- Square RBSOA
- Positive Thermal Coefficient of  $V_{ce(sat)}$
- Anti-Parallel Ultra Fast Diode
- Avalanche Rated
- International Standard Packages

**Advantages**

- High Power Density
- Low Gate Drive Requirement

**Applications**

- High Frequency Power Inverters
- UPS
- Motor Drives
- SMPS
- PFC Circuits
- Battery Chargers
- Welding Machines
- Lamp Ballasts

Symbol	Test Conditions ( $T_J = 25^\circ C$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$BV_{CES}$	$I_C = 250\mu A$ , $V_{GE} = 0V$	950		V
$V_{GE(th)}$	$I_C = 250\mu A$ , $V_{CE} = V_{GE}$	3.5		6.0 V
$I_{CES}$	$V_{CE} = V_{CES}$ , $V_{GE} = 0V$ $T_J = 125^\circ C$			60 $\mu A$ 400 $\mu A$
$I_{GES}$	$V_{CE} = 0V$ , $V_{GE} = \pm 20V$			$\pm 100$ nA
$V_{CE(sat)}$	$I_C = 8A$ , $V_{GE} = 15V$ , Note 1 $T_J = 125^\circ C$	2.15 2.60		2.50 V V

Symbol Test Conditions		Characteristic Values		
(T <sub>J</sub> = 25°C Unless Otherwise Specified)		Min.	Typ.	Max.
<b>g<sub>fs</sub></b>	I <sub>C</sub> = 8A, V <sub>CE</sub> = 10V, Note 1	2.9	4.8	S
<b>C<sub>ies</sub></b>	V <sub>CE</sub> = 25V, V <sub>GE</sub> = 0V, f = 1MHz		400	pF
<b>C<sub>oes</sub></b>			30	pF
<b>C<sub>res</sub></b>			7.8	pF
<b>Q<sub>g(on)</sub></b>	I <sub>C</sub> = 8A, V <sub>GE</sub> = 15V, V <sub>CE</sub> = 0.5 • V <sub>CES</sub>		13.3	nC
<b>Q<sub>ge</sub></b>			3.4	nC
<b>Q<sub>gc</sub></b>			5.8	nC
<b>t<sub>d(on)</sub></b>	Inductive load, T <sub>J</sub> = 25°C I <sub>C</sub> = 8A, V <sub>GE</sub> = 15V V <sub>CE</sub> = 0.5 • V <sub>CES</sub> , R <sub>G</sub> = 30Ω Note 2		16	ns
<b>t<sub>ri</sub></b>			20	ns
<b>E<sub>on</sub></b>			0.46	mJ
<b>t<sub>d(off)</sub></b>			40	ns
<b>t<sub>fi</sub></b>			130	ns
<b>E<sub>off</sub></b>			0.18	0.50 mJ
<b>t<sub>d(on)</sub></b>	Inductive load, T <sub>J</sub> = 125°C I <sub>C</sub> = 8A, V <sub>GE</sub> = 15V V <sub>CE</sub> = 0.5 • V <sub>CES</sub> , R <sub>G</sub> = 30Ω Note 2		17	ns
<b>t<sub>ri</sub></b>			22	ns
<b>E<sub>on</sub></b>			1.00	mJ
<b>t<sub>d(off)</sub></b>			75	ns
<b>t<sub>fi</sub></b>			163	ns
<b>E<sub>off</sub></b>			0.22	mJ
<b>R<sub>thJC</sub></b>	TO-220			1.2 °C/W
<b>R<sub>thCS</sub></b>		0.50		°C/W

**Reverse Diode (FRED)**

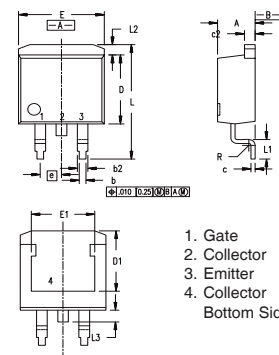
Symbol Test Conditions		Characteristic Value		
(T <sub>J</sub> = 25°C, Unless Otherwise Specified)		Min.	Typ.	Max.
<b>V<sub>F</sub></b>	I <sub>F</sub> = 10A, V <sub>GE</sub> = 0V, Note 1			3.0 V
	T <sub>J</sub> = 150°C			2.0 V
<b>I<sub>RM</sub></b>	I <sub>F</sub> = 10A, V <sub>GE</sub> = 0V, -di <sub>F</sub> /dt = 200A/μs, T <sub>J</sub> = 100°C		7.5	A
<b>t<sub>rr</sub></b>		V <sub>R</sub> = 600V, T <sub>J</sub> = 100°C		114
<b>R<sub>thJC</sub></b>				2.5 °C/W

**Notes:**

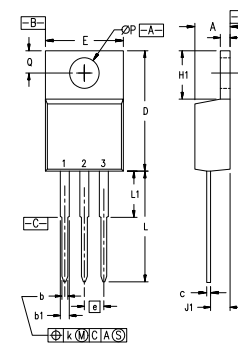
1. Pulse test, t ≤ 300μs, duty cycle, d ≤ 2%.
2. Switching times & energy losses may increase for higher V<sub>CE</sub> (clamp), T<sub>J</sub> or R<sub>G</sub>.

**PRELIMINARY TECHNICAL INFORMATION**

The product presented herein is under development. The Technical Specifications offered are derived from data gathered during objective characterizations of preliminary engineering lots; but also may yet contain some information supplied during a pre-production design evaluation. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

**TO-263 Outline**


Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.06	4.83	.160	.190
b	0.51	0.99	.020	.039
b2	1.14	1.40	.045	.055
c	0.40	0.74	.016	.029
c2	1.14	1.40	.045	.055
D	8.64	9.65	.340	.380
D1	8.00	8.89	.280	.320
E	9.65	10.41	.380	.405
E1	6.22	8.13	.270	.320
e	2.54	BSC	.100	BSC
L	14.61	15.88	.575	.625
L1	2.29	2.79	.090	.110
L2	1.02	1.40	.040	.055
L3	1.27	1.78	.050	.070
L4	0	0.13	0	.005

**TO-220 Outline**


Pins: 1 - Gate 2 - Collector  
3 - Emitter

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.170	.190	4.32	4.83
b	.025	.040	0.64	1.02
b1	.045	.065	1.15	1.65
c	.014	.022	0.35	0.56
D	.580	.630	14.73	16.00
E	.390	.420	9.91	10.66
e	.100	BSC	2.54	BSC
F	.045	.055	1.14	1.40
H1	.230	.270	5.85	6.85
J1	.090	.110	2.29	2.79
k	0	.015	0	0.38
L	.500	.550	12.70	13.97
L1	.110	.230	2.79	5.84
ØP	.139	.161	3.53	4.08
Q	.100	.125	2.54	3.18

**IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.**

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

Fig. 1. Output Characteristics @  $T_J = 25^\circ\text{C}$

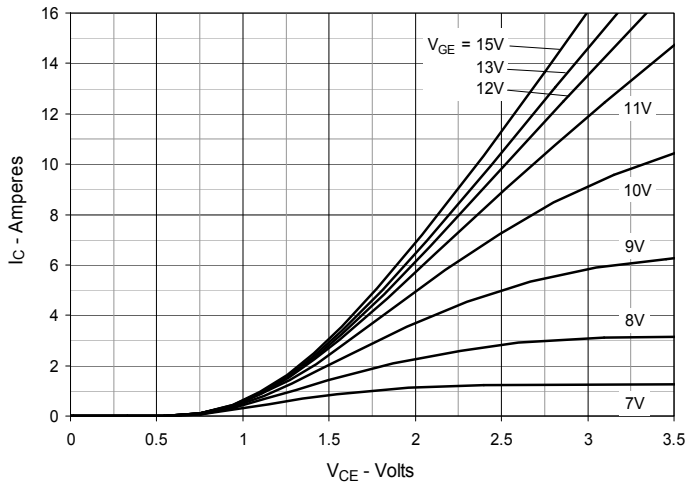


Fig. 2. Extended Output Characteristics @  $T_J = 25^\circ\text{C}$

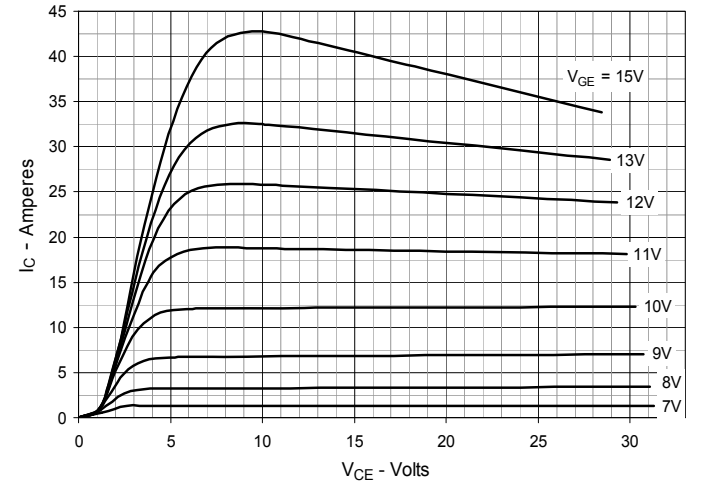


Fig. 3. Output Characteristics @  $T_J = 150^\circ\text{C}$

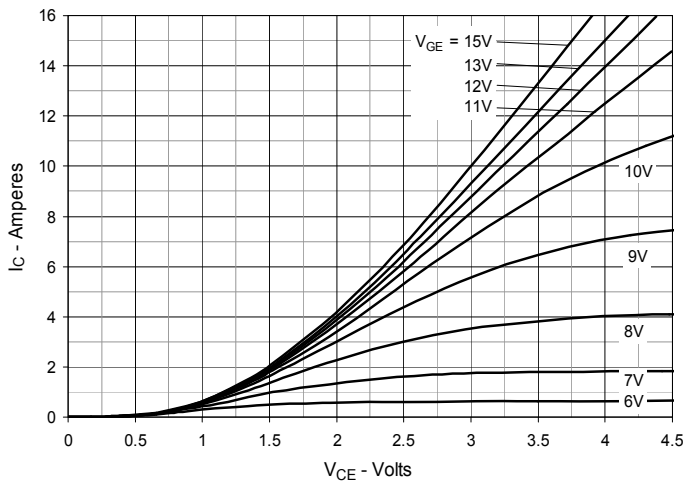


Fig. 4. Dependence of  $V_{CE(sat)}$  on Junction Temperature

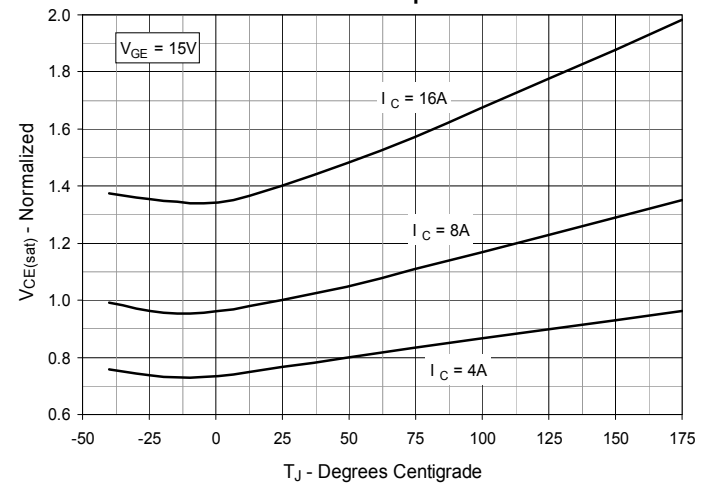


Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

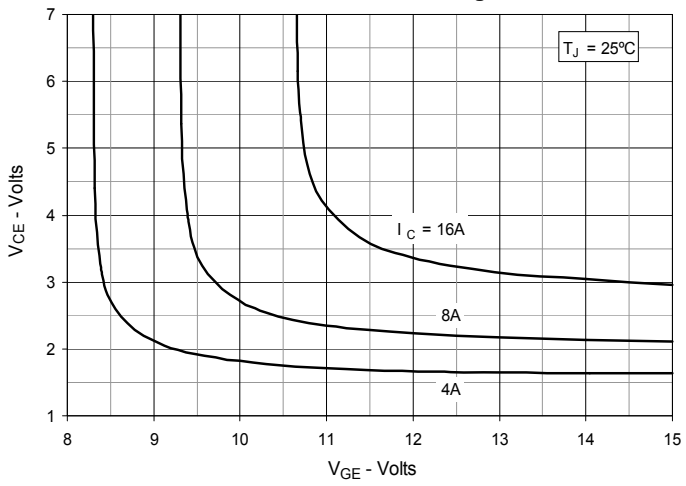


Fig. 6. Input Admittance

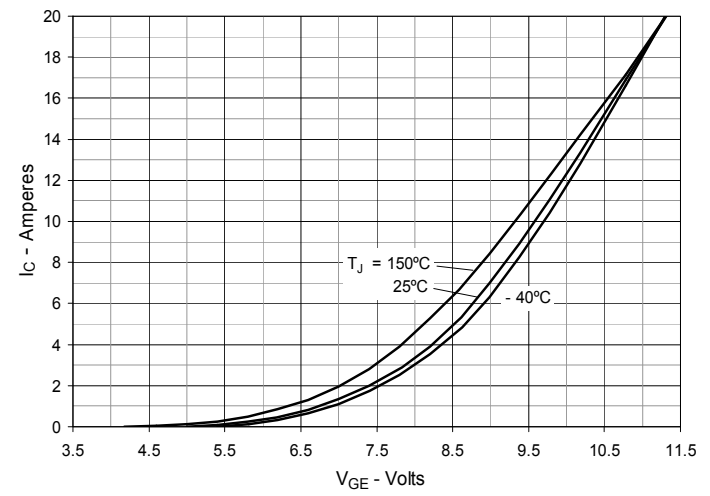


Fig. 7. Transconductance

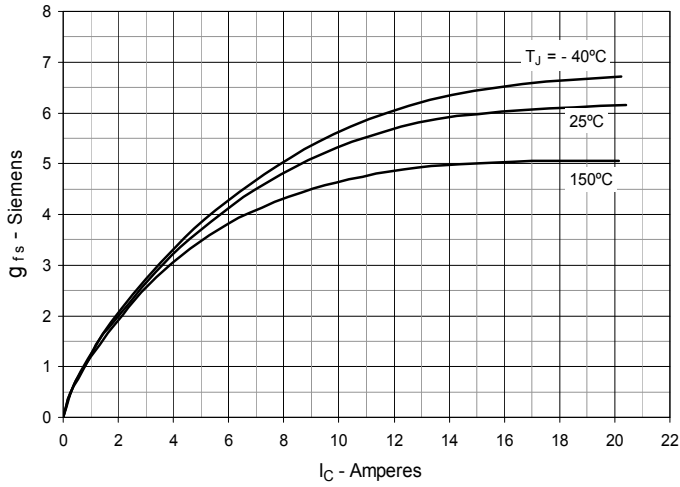


Fig. 8. Gate Charge

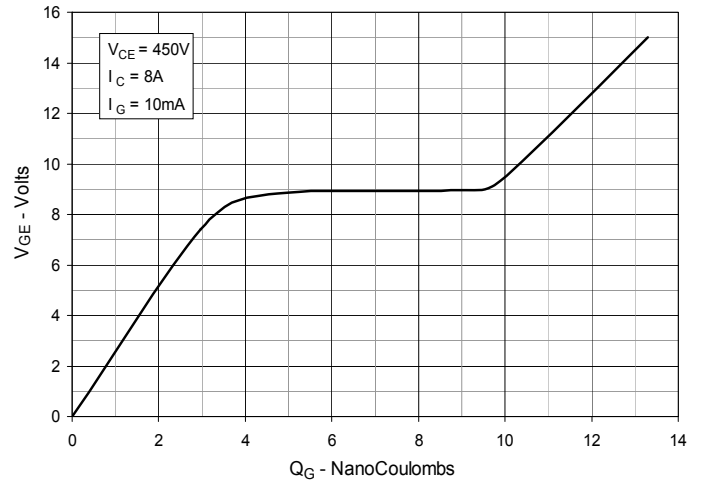


Fig. 9. Capacitance

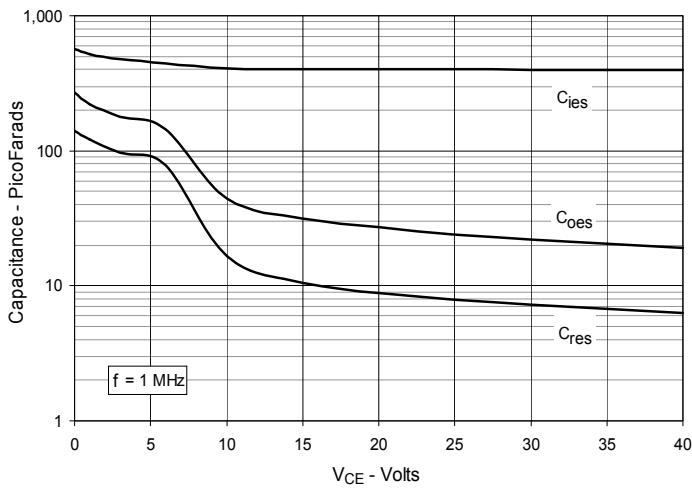


Fig. 10. Reverse-Bias Safe Operating Area

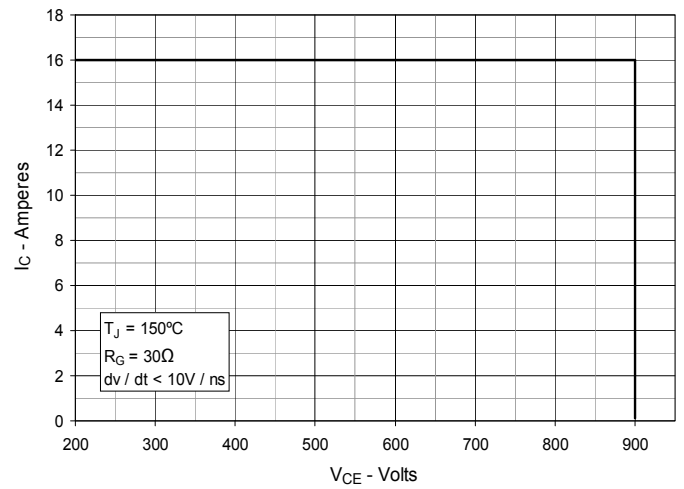
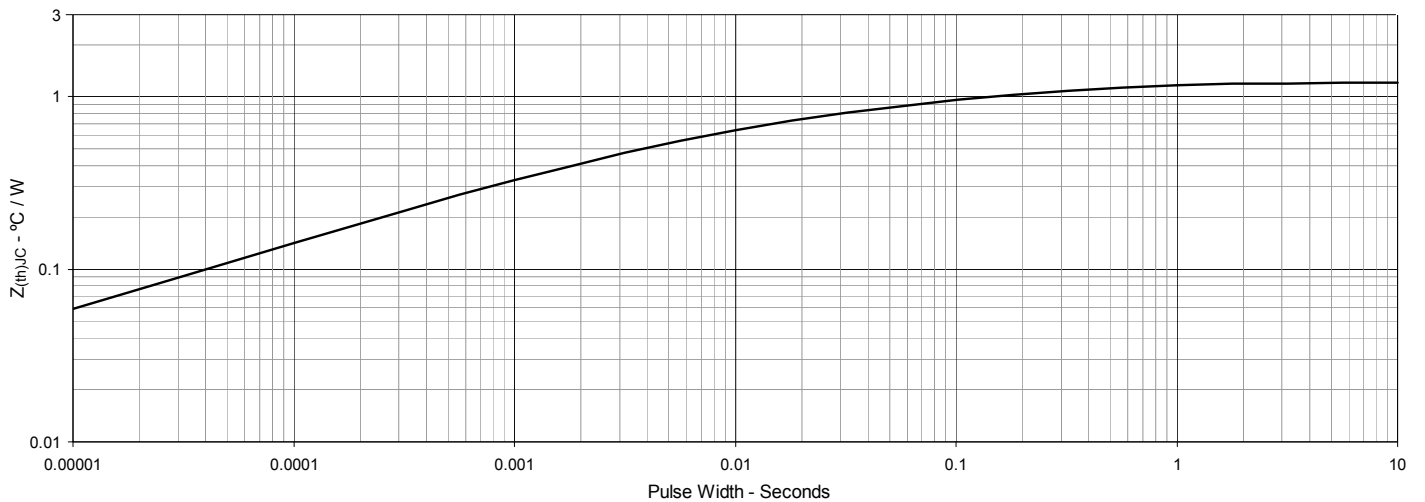
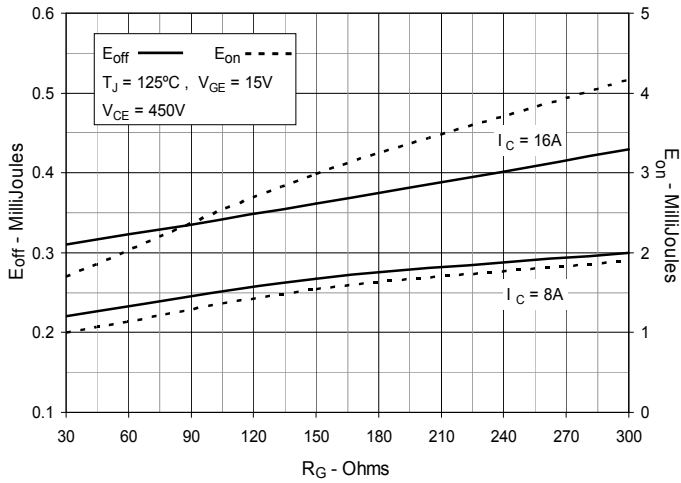


Fig. 11. Maximum Transient Thermal Impedance

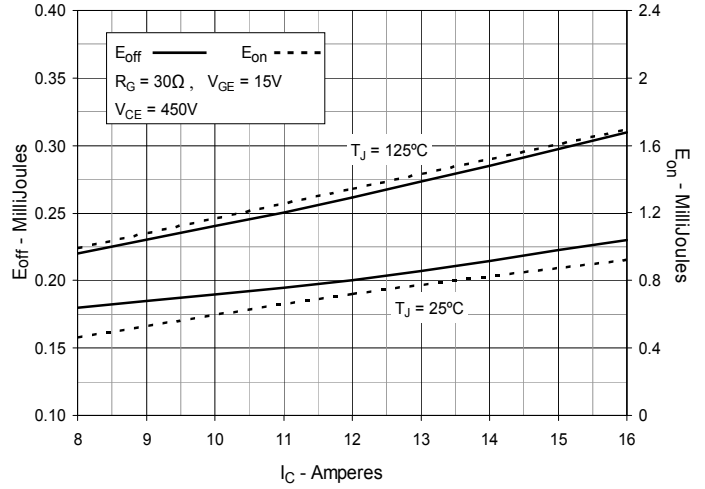


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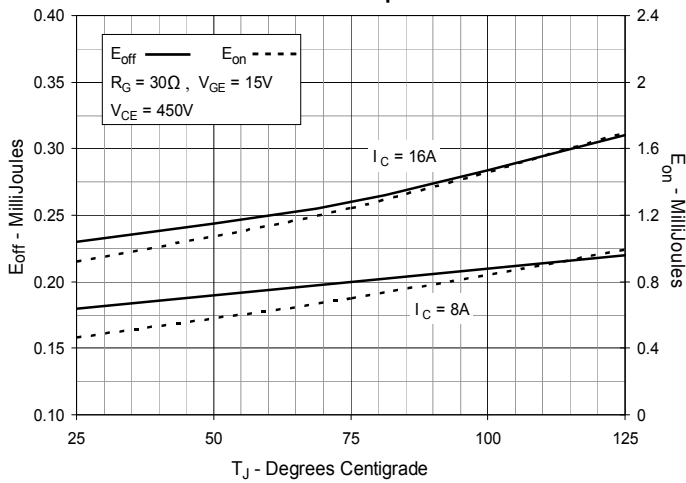
**Fig. 12. Inductive Switching Energy Loss vs. Gate Resistance**



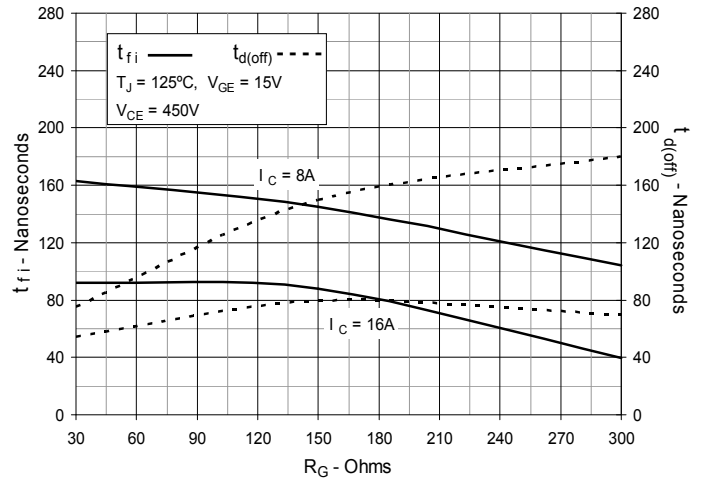
**Fig. 13. Inductive Switching Energy Loss vs. Collector Current**



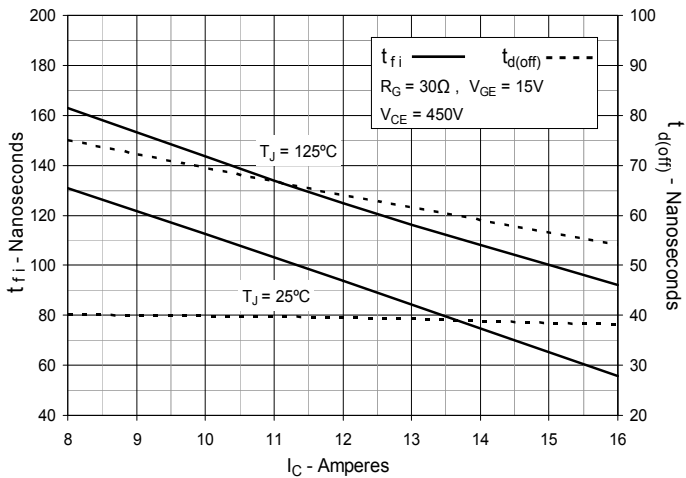
**Fig. 14. Inductive Switching Energy Loss vs. Junction Temperature**



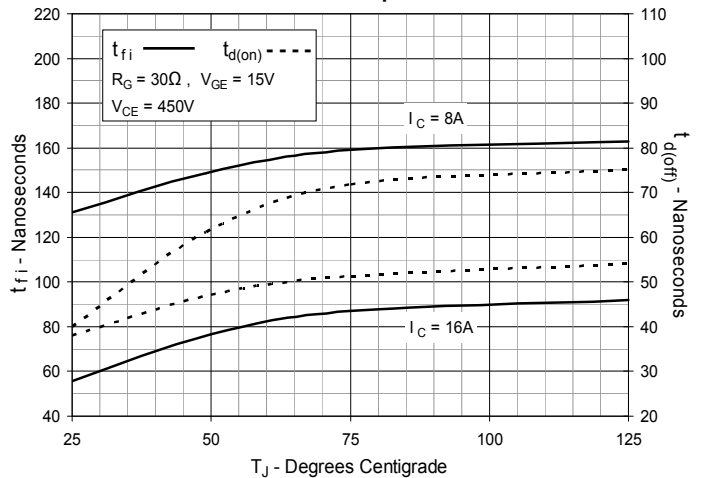
**Fig. 15. Inductive Turn-off Switching Times vs. Gate Resistance**



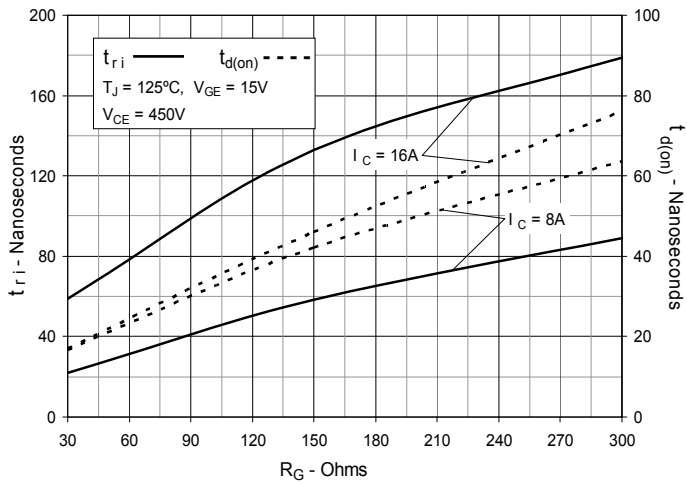
**Fig. 16. Inductive Turn-off Switching Times vs. Collector Current**



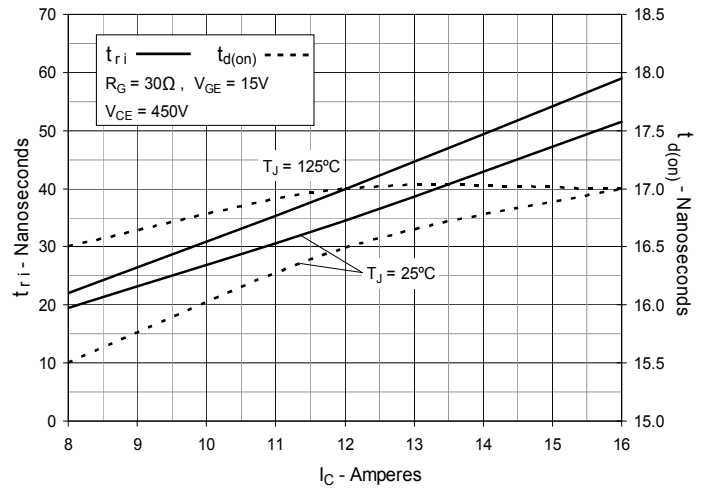
**Fig. 17. Inductive Turn-off Switching Times vs. Junction Temperature**



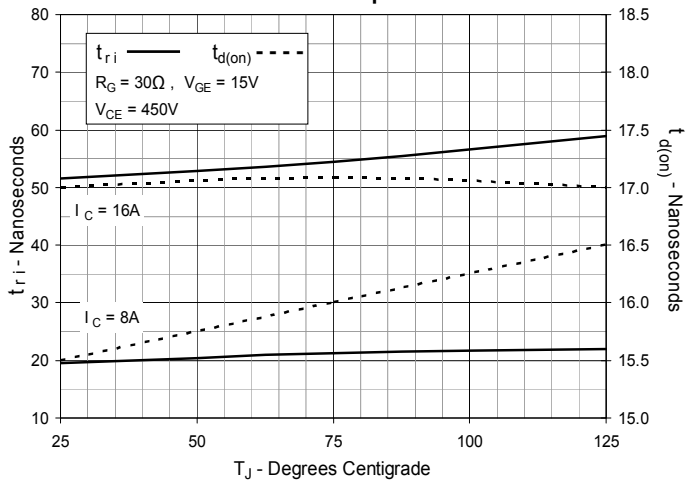
**Fig. 18. Inductive Turn-on Switching Times vs. Gate Resistance**



**Fig. 19. Inductive Turn-on Switching Times vs. Collector Current**



**Fig. 20. Inductive Turn-on Switching Times vs. Junction Temperature**



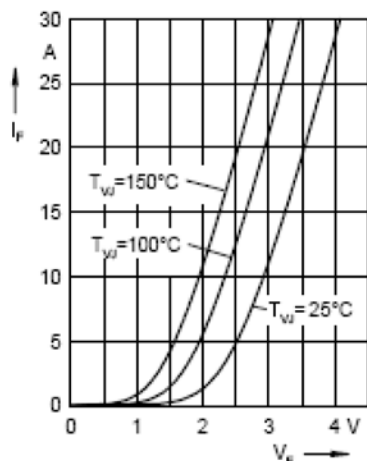


Fig. 21. Forward current  $I_F$  vs  $V_F$

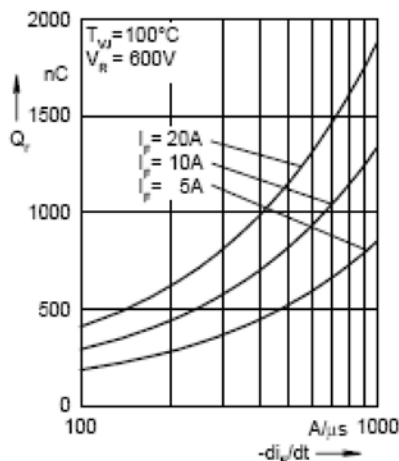


Fig. 22. Reverse recovery charge  $Q_r$  versus  $-di_F/dt$

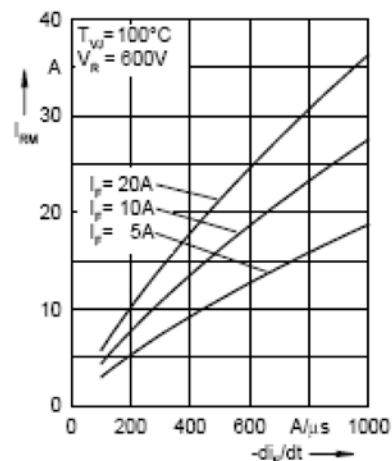


Fig. 23. Peak reverse current  $I_{RM}$  versus  $-di_F/dt$

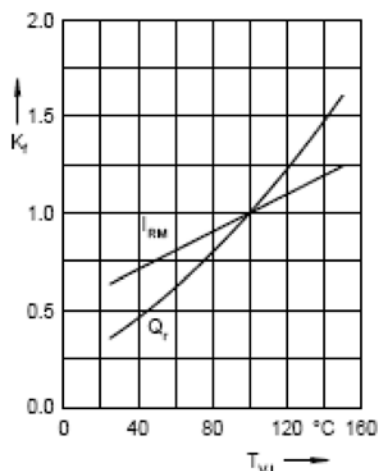


Fig. 24. Dynamic parameters  $Q_r$ ,  $I_{RM}$  versus  $T_{vj}$

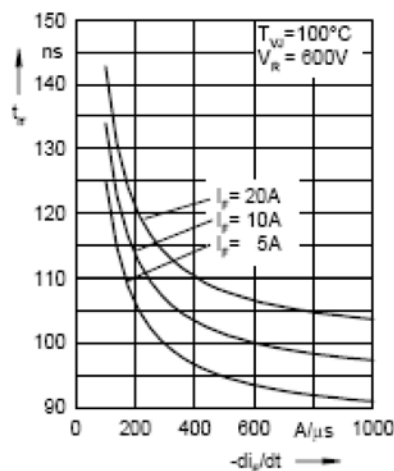


Fig. 25. Recovery time  $t_r$  versus  $-di_F/dt$

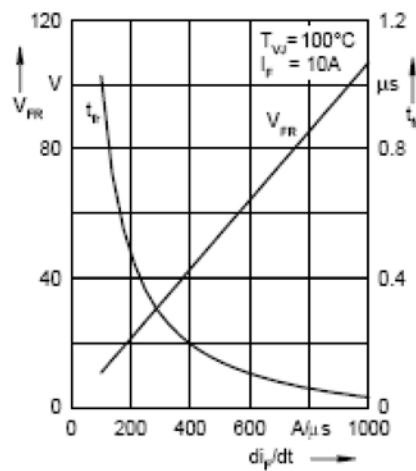


Fig. 26. Peak forward voltage  $V_{FR}$  and  $t_{fr}$  versus  $di_F/dt$

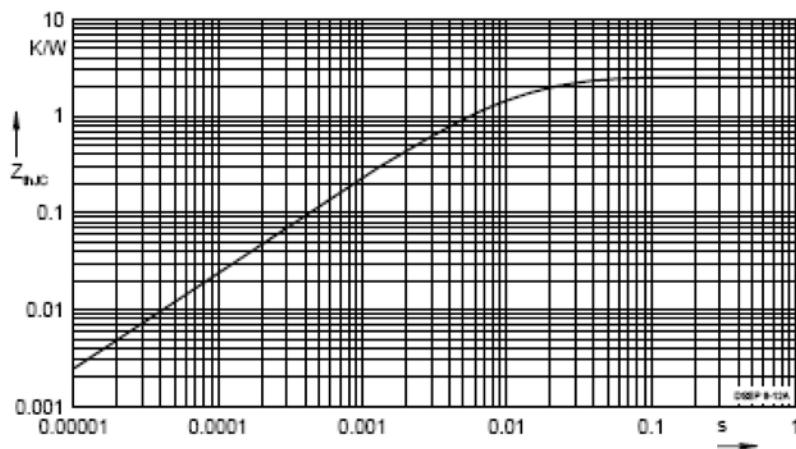


Fig. 27. Transient thermal resistance junction to case